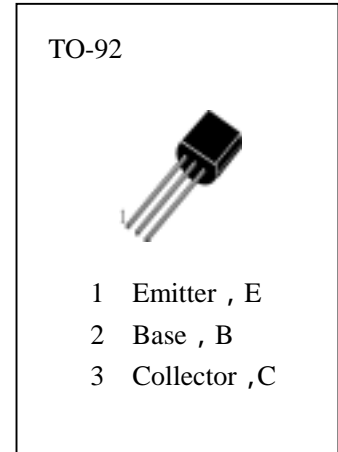




HIGH VOLTAGE TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (Ta=25)

- T_{stg}—Storage Temperature..... -55~150
- T_j—Junction Temperature.....150
- P_C—Collector Dissipation.....625mW
- V_{CBO}—Collector-Base Voltage.....500V
- V_{CEO}—Collector-Emitter Voltage.....400V
- V_{EBO}—Emitter-Base Voltage.....6V
- I_C—Collector Current.....300mA



ELECTRICAL CHARACTERISTICS (Ta=25)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	500			V	I _C =100 μ A, I _E =0
BVCEO	Collector-Emitter Breakdown Voltage	400			V	I _C =1mA, I _B =0
BVEBO	Emitter-Base Breakdown Voltage	6			V	I _E =100 μ A , I _C =0
ICBO	Collector Cut-off Current			100	nA	V _{CB} =400V, I _E =0
IEBO	Emitter-Base Cut-off Current			100	nA	V _{EB} =4V, I _C =0
ICES	Collector Cut-off Current			500	nA	V _{CE} =-400V, V _{BE} =0
HFE (1)	DC Current Gain	40				V _{CE} =10V, I _C =1mA
HFE (2)		60		300		V _{CE} =10V, I _C =10mA
HFE (3)		45				V _{CE} =10V, I _C =50mA
HFE (4)		40				V _{CE} =10V, I _C =100mA
VCE(sat1)	Collector- Emitter Saturation Voltage			0.4	V	I _C =1mA, I _B =0.1mA
VCE(sat2)				0.5	V	I _C =10mA, I _B =1mA
VCE(sat3)				0.75	V	I _C =50mA, I _B =5mA
VBE(sat)	Base-Emitter Saturation Voltage			0.75	V	I _C =10mA, I _B =1mA
Cob	Output Capacitance	7			ρF	V _{CB} =20V, I _E =0 ,F=1MHz